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CENTRAL FAX CENTER  
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ABSTRACT OF THE DISCLOSURE

- A method and a system for improving the strength of connection  
between a dielectric carrier substrate and a cover layer by obliquely  
5 bombarding the substrate at at least one of its surfaces with high energy  
heavy ion irradiation from two different angles to produce intersecting latent  
ion traces therein which by subsequent chemical etching are formed into  
intersecting recesses within which the cover layer may be anchored.